

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Advanced trench cell design
- ☒ Low Thermal Resistance

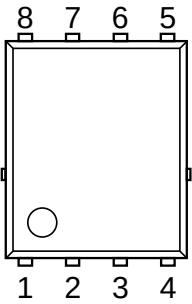
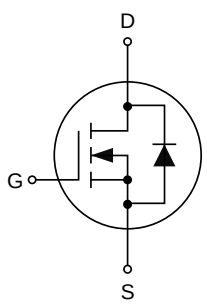
1.2 Applications

- ☒ Motor drivers
- ☒ DC/DC Converter

1.3 Quick reference

- ☒ $BV \geq 40\text{ V}$
- ☒ $P_{tot} \leq 78\text{ W}$
- ☒ $I_D \leq 164\text{ A}$
- ☒ $R_{DS(ON)} \leq 2.3\text{ m}\Omega @V_{GS} = 10\text{ V}$
- ☒ $R_{DS(ON)} \leq 3.5\text{ m}\Omega @V_{GS} = 4.5\text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source	 Top View PDFN5x6-8L	
4	Gate		
5,6,7,8	Drain		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	40	-	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 20	V
I_D^*	Drain Current (DC)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	164	A
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	103	A
$I_{DM}^{*,**}$	Pulsed Source Current	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	656	A
P_{tot}^*	Total Power Dissipation	$T_C=25^{\circ}\text{C}$	-	78	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55	150	$^{\circ}\text{C}$
I_S	Diode Forward Current	$T_C=25^{\circ}\text{C}$	-	164	A
E_{AS}^*	Single Pulsed Avalanche Energy	$V_{DD}=40\text{ V}, L=1.0\text{ mH}$	-	364	mJ
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient		-	39.9	$^{\circ}\text{C/W}$
$R_{\theta JC}^*$	Thermal Resistance-Junction to Case		-	1.6	

Notes:

- * Surface mounted on 1 in² pad area, $t \leq 10\text{ sec}$.
- ** Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- *** Limited by bonding wire.

4. Marking Information

Product Name	Marking
KJ2R2N04G	2R2N04 YWWXXX YWWXXX: Date Code

5. Ordering Code

Product Name	Package	Reel size	Tape width	Quantity (pcs)
KJ2R2N04G	PDFN 5x6-8L	13"	12 mm	5000

Note: KUAIJIE XIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

6. Electrical Characteristics (T_A=25°C unless otherwise noted)

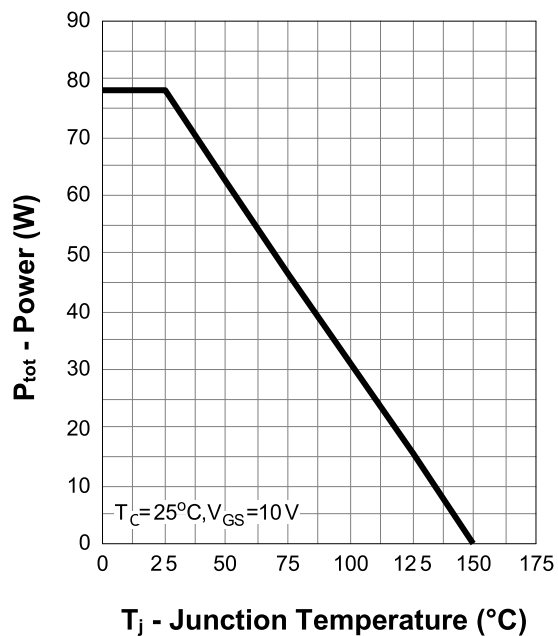
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	40	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	1	-	3	V
I _{DSS}	Zero Gate Voltage Source Current	V _{DS} =32 V, V _{GS} =0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{DS} =0 V, V _{GS} =±20 V	-	-	±100	nA
R _{DS(ON)} ^a	On-State Resistance	V _{GS} =10 V, I _{DS} =10 A	-	2.0	2.3	mΩ
		V _{GS} =4.5 V, I _{DS} =10 A	-	3.0	3.5	
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =10 A, V _{GS} =0 V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _{DS} =10 A, V _{GS} =0 V, dI _{SD} /dt=100 A/μs	-	39	-	ns
Q _{rr}	Reverse Recovery Charge		-	24	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0 V, V _{DS} =20 V, Frequency=1 MHz	-	2578	-	pF
C _{oss}	Output Capacitance		-	1574	-	
C _{rss}	Reverse Transfer Capacitance		-	310	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =20 V, V _{GEN} =10 V, R _G =3.9 Ω, R _L =0.66 Ω, I _{DS} =10 A	-	9.1	-	ns
t _r	Turn-on Rise Time		-	64	-	
t _{d(off)}	Turn-off Delay Time		-	48	-	
t _f	Turn-off Fall Time		-	38	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =20 V, V _{GS} =10 V, I _{DS} =10 A	-	51	-	nC
Q _{gs}	Gate-Source Charge		-	11	-	
Q _{gd}	Gate-Drain Charge		-	10	-	

Notes:

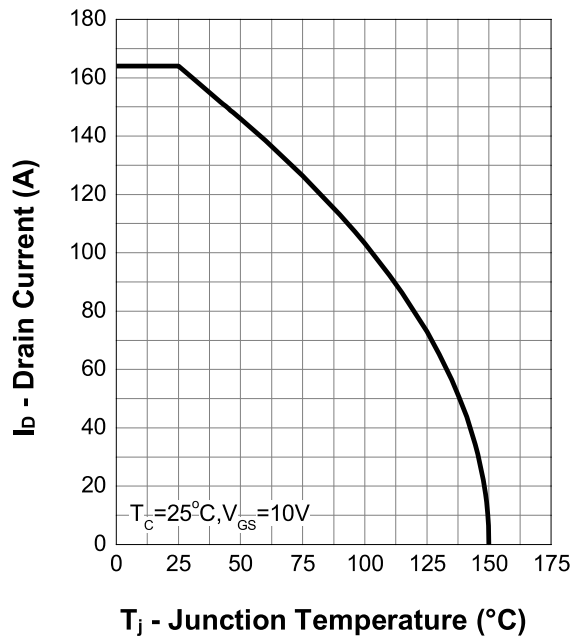
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

7. Typical Characteristics

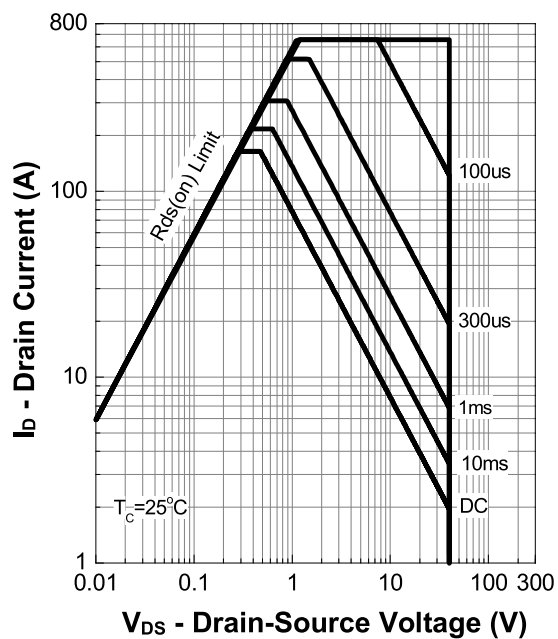
Power Capability



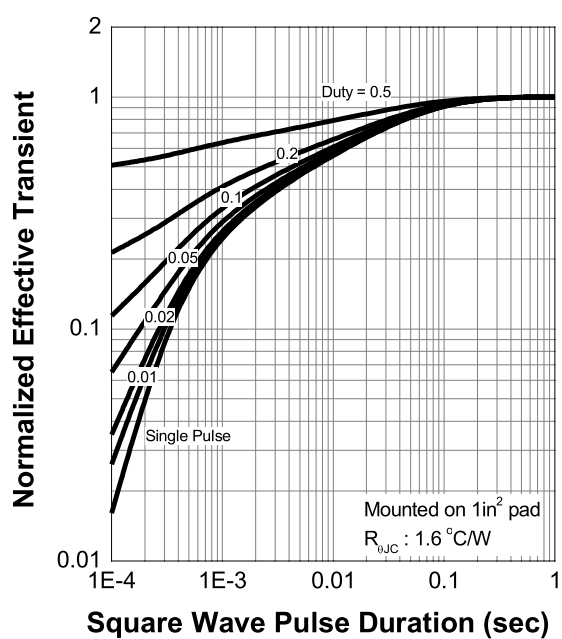
Current Capability



Safe Operation Area

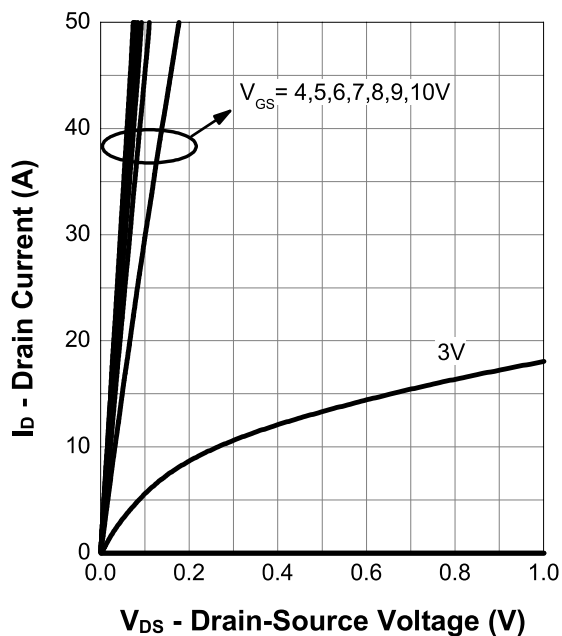


Transient Thermal Impedance

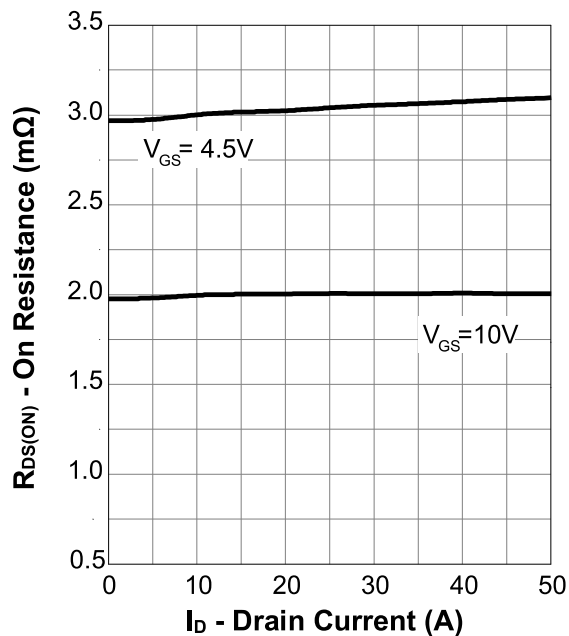


7. Typical Characteristics (cont.)

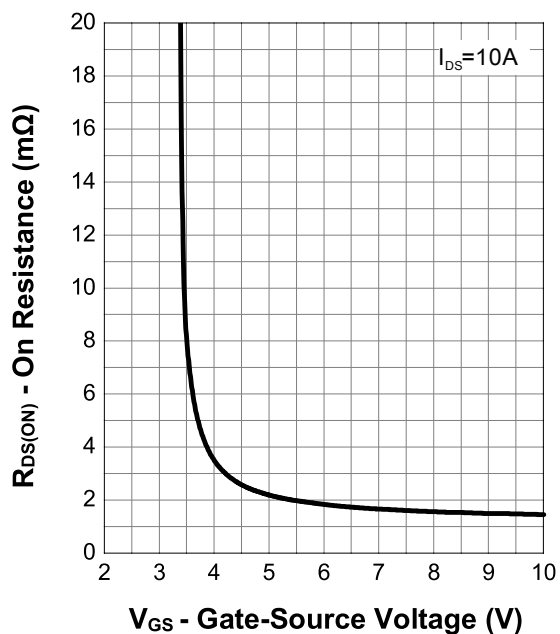
Output Characteristics



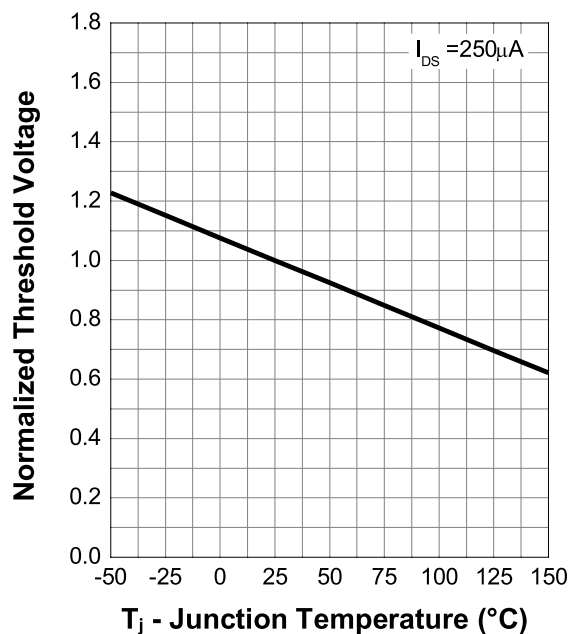
On Resistance



Transfer Characteristics

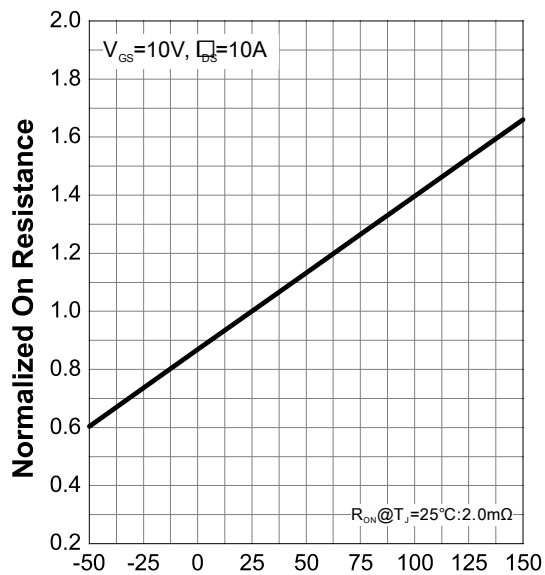


Normalized Threshold Voltage



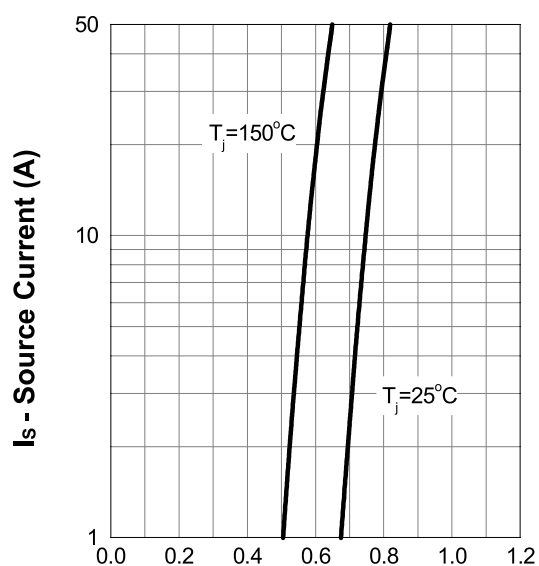
7. Typical Characteristics (cont.)

Normalized On Resistance



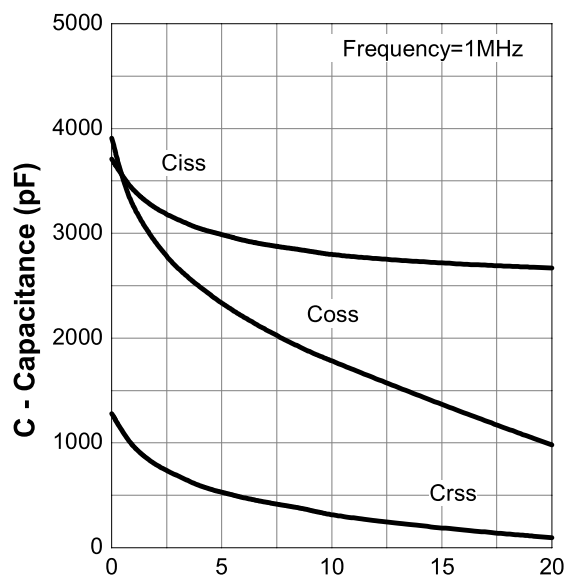
T_j - Junction Temperature ($^{\circ}\text{C}$)

Diode Forward Current



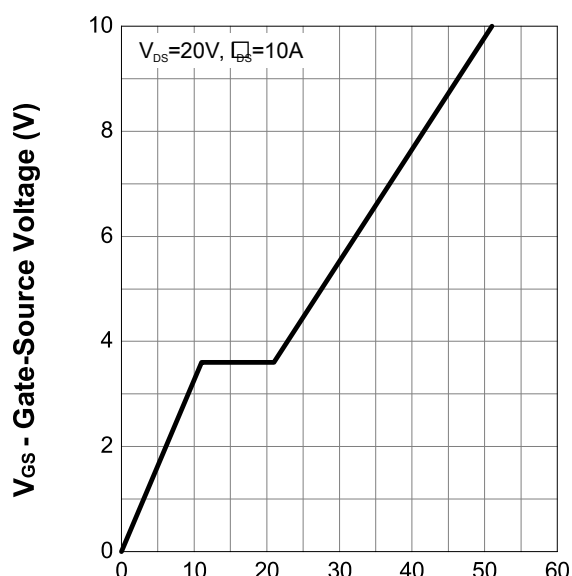
V_{SD} - Source-Drain Voltage (V)

Capacitance



V_{DS} - Drain-Source Voltage (V)

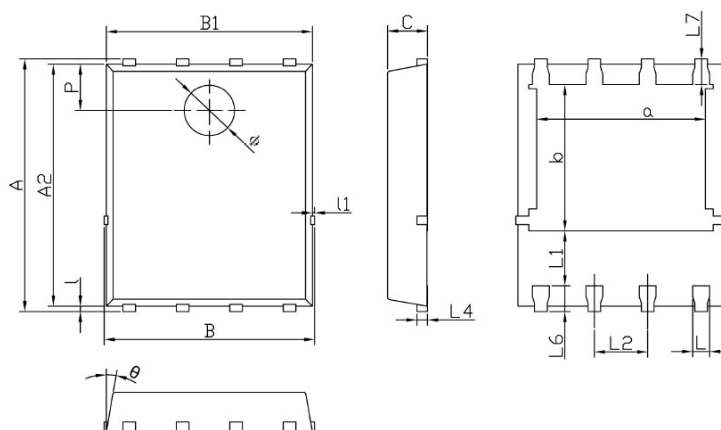
Gate Charge



Q_G - Gate Charge (nC)

8. Package Dimensions

PDFN 5x6-8L Package



Symbol	Dimensions in Millimeters		
	MIN	TYP	MAX
A	5.90	6.00	6.10
a	3.91	4.01	4.11
A2	5.70	5.75	5.80
B	4.90	5.00	5.10
b	3.37	3.47	3.57
B1	4.80	4.90	5.00
C	0.90	0.95	1.00
L	0.35	0.40	0.45
l	0.06	0.13	0.20
L1	1.10	-	-
l1	-	-	0.10
L2	1.17	1.27	1.37
L4	0.21	0.26	0.34
L6	0.51	0.61	0.71
L7	0.51	0.61	0.71
P	1.00	1.10	1.20
θ	8°	10°	12°
Φ	1.10	1.20	1.30